

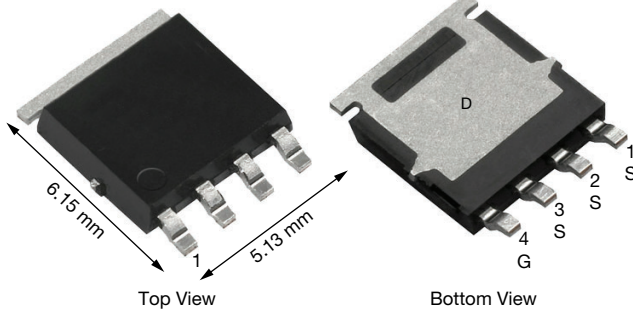
## N-Channel 40 V (D-S) MOSFET



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A) <sup>a, g</sup>	Q <sub>g</sub> (Typ.)
40	0.00135 at V <sub>GS</sub> = 10 V	80	58 nC
	0.00175 at V <sub>GS</sub> = 4.5 V	80	

PowerPAK® SO-8L Single



### Ordering Information:

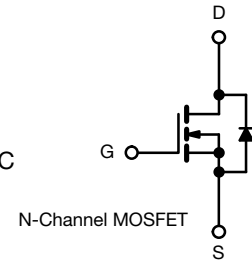
SiJ438DP-T1-GE3 (lead (Pb)-free and halogen-free)

### FEATURES

- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R<sub>DS</sub>-Q<sub>oss</sub> FOM
- 100 % R<sub>g</sub> and UIS tested
- Q<sub>gd</sub> / Q<sub>gs</sub> ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### APPLICATIONS

- Synchronous rectification
- ORing
- High power density DC/DC
- VRMs and embedded DC/DC
- DC/AC inverters
- Load switch



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	+20, -16	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	80 <sup>g</sup>
		T <sub>C</sub> = 70 °C	80 <sup>g</sup>
		T <sub>A</sub> = 25 °C	45.3 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	36.2 <sup>b, c</sup>
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	200	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	4.5 <sup>b, c</sup>
Single Pulse Avalanche Current	I <sub>AS</sub>	50	mJ
Single Pulse Avalanche Energy	E <sub>AS</sub>	125	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	69.4
		T <sub>C</sub> = 70 °C	44.4
		T <sub>A</sub> = 25 °C	5 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	3.2 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, f</sup>	R <sub>thJA</sub>	20	25	°C/W
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	1.3	1.8	

### Notes

- T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 65 °C/W.
- Package limited.



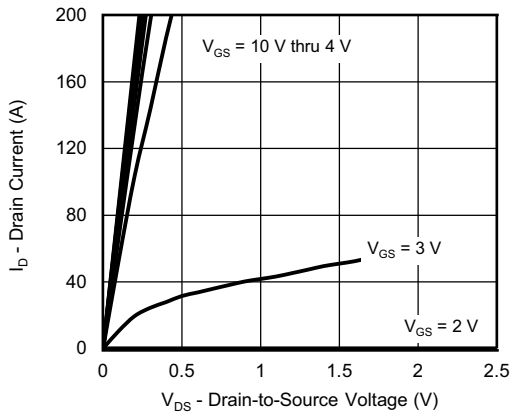
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	40	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	22	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-5.6	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.1	-	2.4	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +20 V, -16 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.00110	0.00135	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	0.00145	0.00175	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A	-	149	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	9400	-	pF
Output Capacitance	C <sub>OSS</sub>		-	1340	-	
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	215	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	-	121	182	nC
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	58	87	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	22.6	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	13.5	-	
Output Charge	Q <sub>OSS</sub>		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	-	62.5	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.4	1.1	2.0	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	16	32	ns
Rise Time	t <sub>r</sub>		-	19	38	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	54	108	
Fall Time	t <sub>f</sub>		-	9	18	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	55	110	ns
Rise Time	t <sub>r</sub>		-	98	196	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	47	94	
Fall Time	t <sub>f</sub>		-	17	34	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	63	A
Pulse Diode Forward Current (t = 100 μs)	I <sub>SM</sub>		-	-	200	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	-	0.7	1.1	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	60	120	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	95	190	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	33	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	27	-	

**Notes**

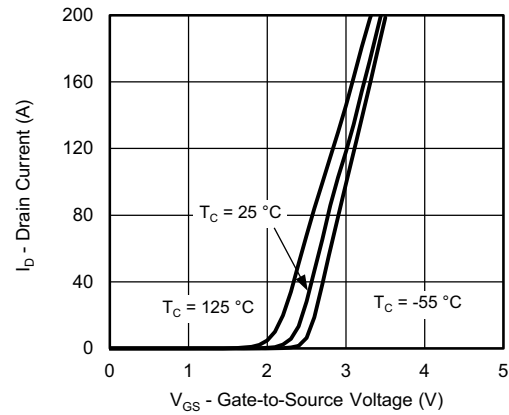
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

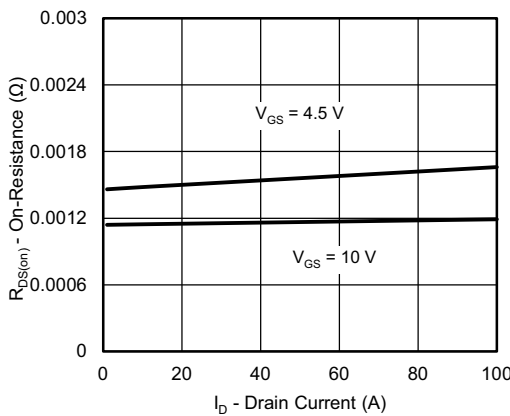
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



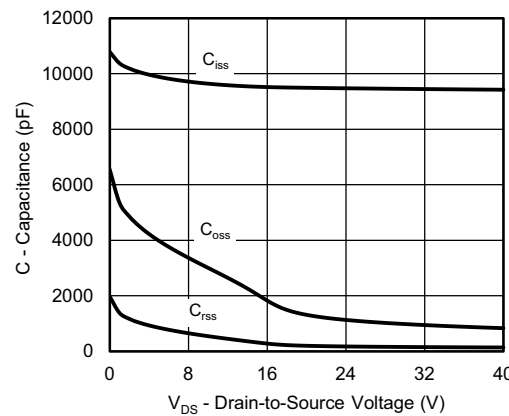
**Output Characteristics**



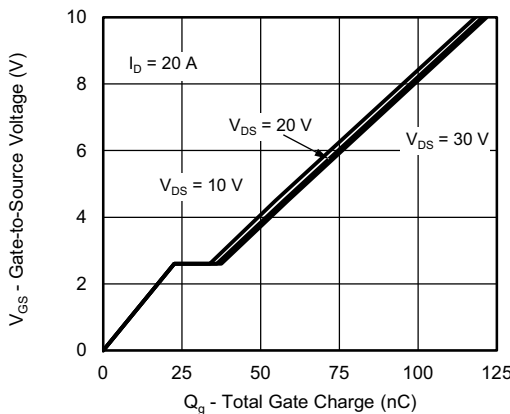
**Transfer Characteristics**



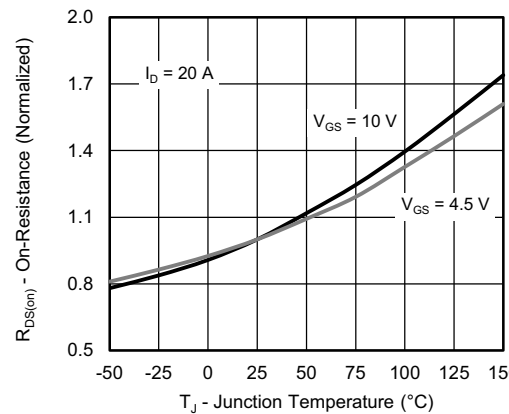
**On-Resistance vs. Drain Current**



**Capacitance**



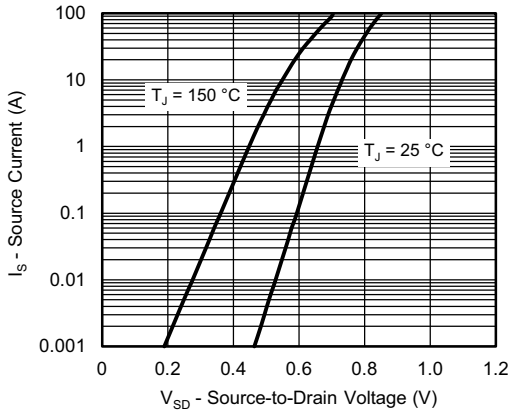
**Gate Charge**



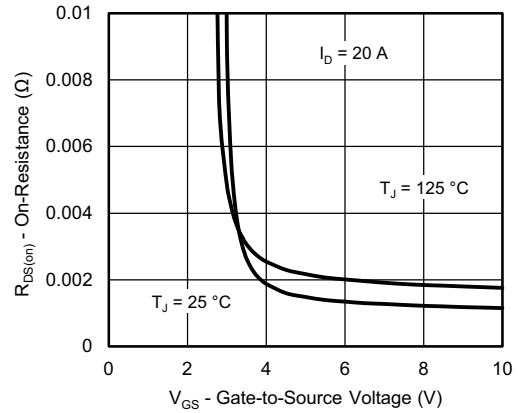
**On-Resistance vs. Junction Temperature**



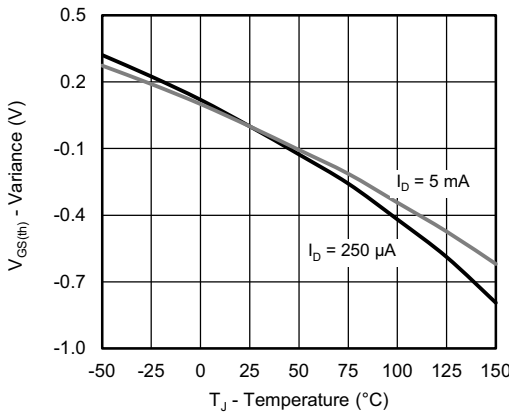
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



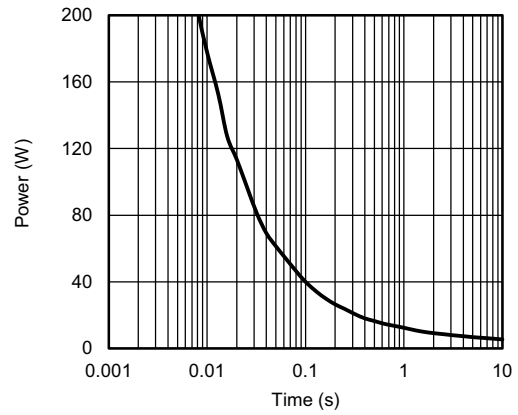
Source-Drain Diode Forward Voltage



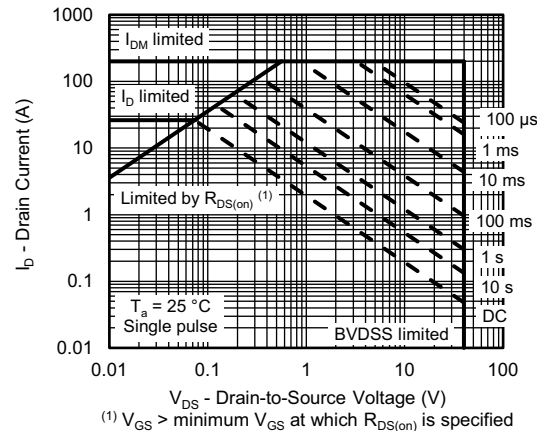
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



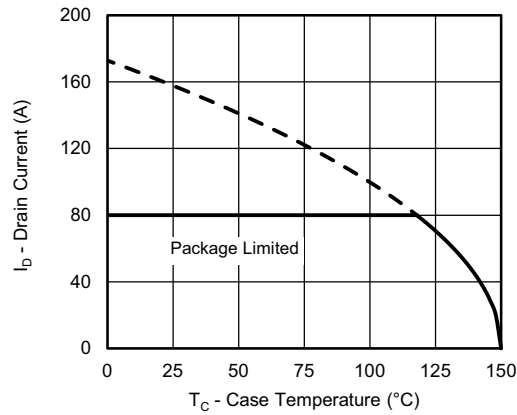
Single Pulse Power, Junction-to-Ambient



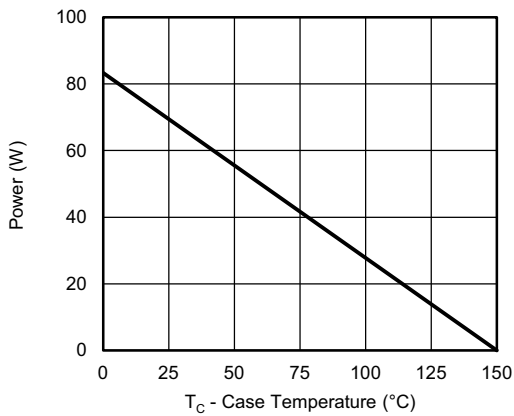
Safe Operating Area, Junction-to-Ambient



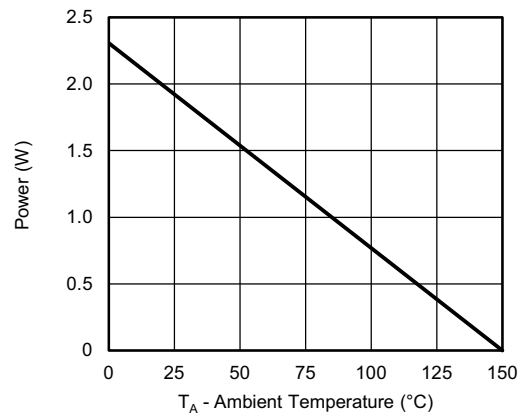
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



**Power, Junction-to-Case**



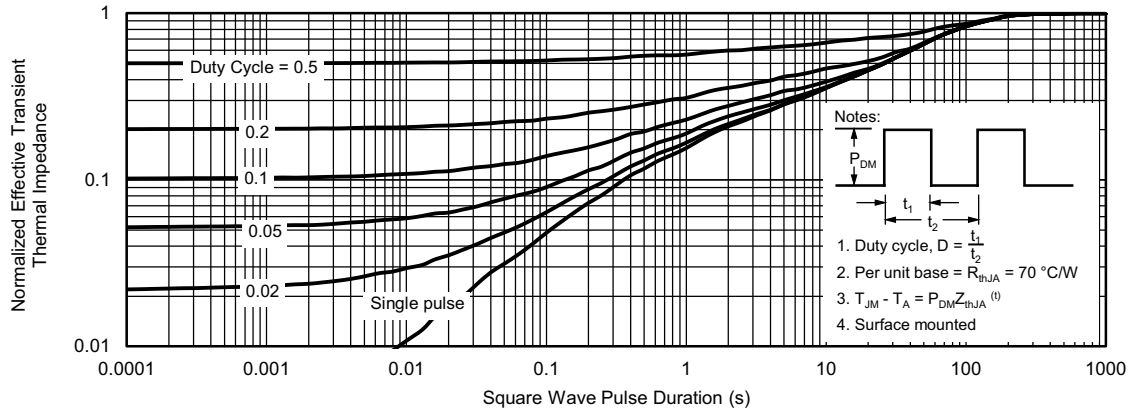
**Power, Junction-to-Ambient**

**Note**

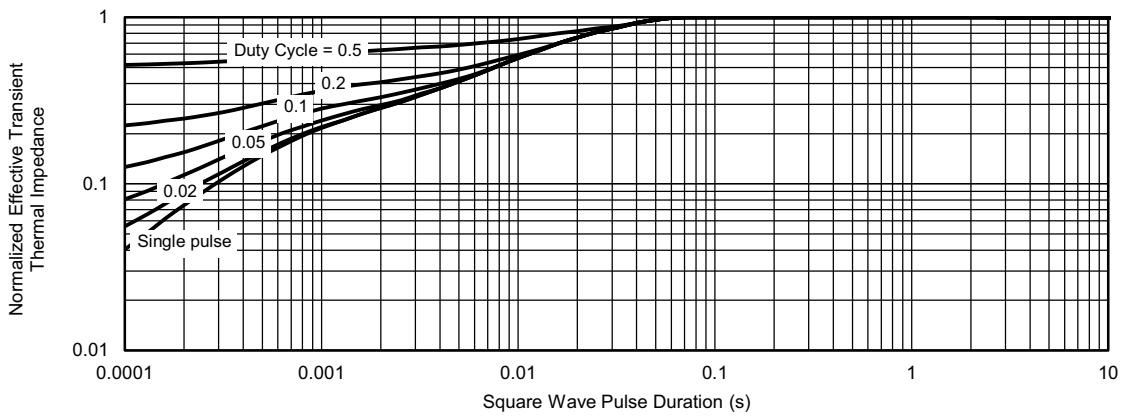
a. The power dissipation  $P_D$  is based on  $T_J$  (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

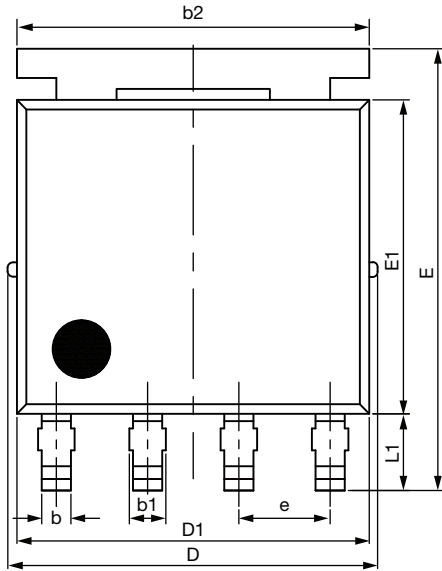


**Normalized Thermal Transient Impedance, Junction-to-Case**

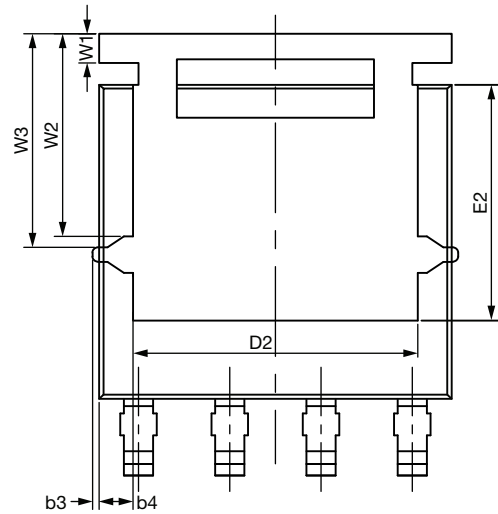
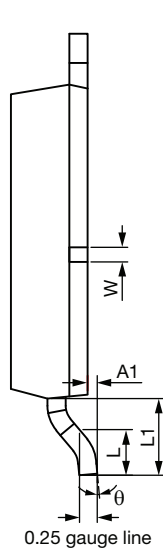
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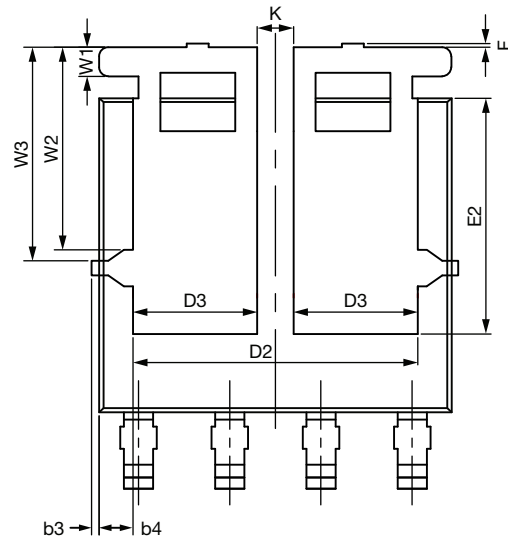
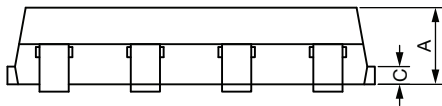
# PowerPAK® SO-8L Case Outline for Non-AI Parts



Topside view



Backside view (single)



Backside view (dual)



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: T16-0221-Rev. D, 16-May-16 DWG: 5976						

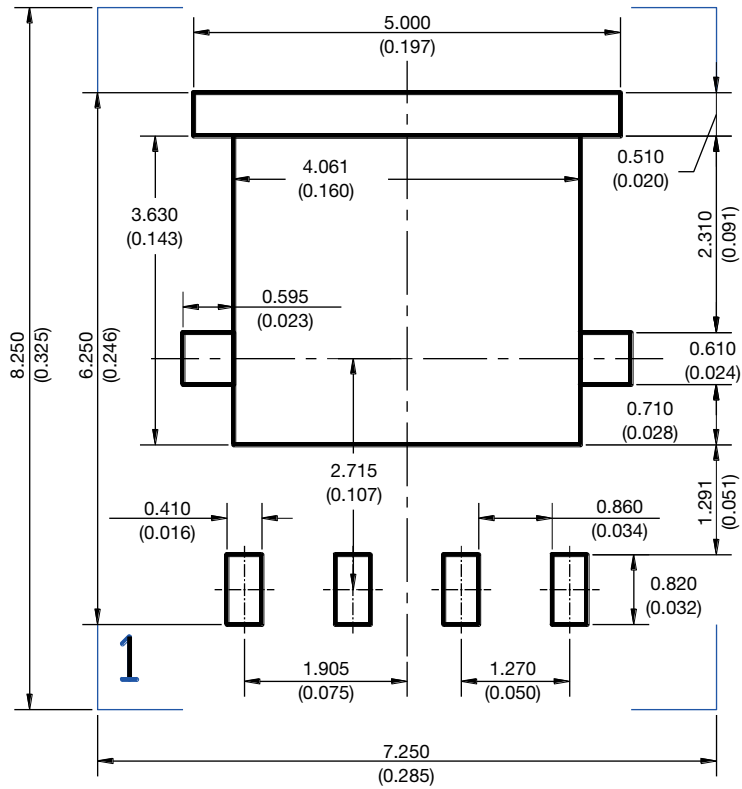
**Note**

- Millimeters will govern





**RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE**



Recommended Minimum Pads  
Dimensions in mm (inches)



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